Zi-Hui Zhang

List of Publications by Citations

139 papers	1,789 citations	24 h-index	35 g-index
148 ext. papers	2,236 ext. citations	3.9 avg, IF	4.84 L-index

#	Paper	IF	Citations
139	Unambiguously Enhanced Ultraviolet Luminescence of AlGaN Wavy Quantum Well Structures Grown on Large Misoriented Sapphire Substrate. *Advanced Functional Materials*, **2019**, 29, 1905445	15.6	85
138	InGaN/GaN light-emitting diode with a polarization tunnel junction. *Applied Physics Letters*, **2013**, 102, 193508	3.4	78
137	Graphene-based transparent conductive electrodes for GaN-based light emitting diodes: Challenges and countermeasures. *Nano Energy*, **2015**, 12, 419-436	17.1	73
136	Hole Transport Manipulation To Improve the Hole Injection for Deep Ultraviolet Light-Emitting Diodes. *ACS Photonics*, **2017**, 4, 1846-1850	6.3	72
135	Impact of the surface recombination on InGaN/GaN-based blue micro-light emitting diodes. *Optics Express*, **2019**, 27, A643-A653	3.3	58
134	Orange to Red, Emission-Tunable Mn-Doped Two-Dimensional Perovskites with High Luminescence and Stability. *ACS Applied Materials & Interfaces*, **2019**, 11, 34109-34116	9.5	45
133	One Stone, Two Birds: High-Efficiency Blue-Emitting Perovskite Nanocrystals for LED and Security Ink Applications. *Chemistry of Materials*, **2019**, 31, 5116-5123	9.6	43
132	Self-screening of the quantum confined Stark effect by the polarization induced bulk charges in the quantum barriers. *Applied Physics Letters*, **2014**, 104, 243501	3.4	42
131	On the Effect of Step-Doped Quantum Barriers in InGaN/GaN Light Emitting Diodes. *Journal of Display Technology*, **2013**, 9, 226-233		42
130	On the electric-field reservoir for III-nitride based deep ultraviolet light-emitting diodes. *Optics Express*, **2017**, 25, 16550-16559	3.3	40
129	On the origin of enhanced hole injection for AlGaN-based deep ultraviolet light-emitting diodes with AlN insertion layer in p-electron blocking layer. *Optics Express*, **2019**, 27, A620-A628	3.3	39
128	Improved InGaN/GaN light-emitting diodes with a p-GaN/n-GaN/p-GaN/n-GaN/p-GaN current-spreading layer. *Optics Express*, **2013**, 21, 4958-69	3.3	37
127	High-efficiency all-inorganic full-colour quantum dot light-emitting diodes. *Nano Energy*, **2018**, 46, 229-233	17.1	33
126	Improving hole injection efficiency by manipulating the hole transport mechanism through p-type electron blocking layer engineering. *Optics Letters*, **2014**, 39, 2483-6	3	33
125	Nearly Efficiency-Droop-Free AlGaN-Based Ultraviolet Light-Emitting Diodes with a Specifically Designed Superlattice p-Type Electron Blocking Layer for High Mg Doping Efficiency. *Nanoscale Research Letters*, **2018**, 13, 122	5	32
124	Increasing the hole energy by grading the alloy composition of the p-type electron blocking layer for very high-performance deep ultraviolet light-emitting diodes. *Photonics Research*, **2019**, 7, B1	6	32
123	A hole accelerator for InGaN/GaN light-emitting diodes. *Applied Physics Letters*, **2014**, 105, 153503	3.4	29

122	Enhanced hole transport in InGaN/GaN multiple quantum well light-emitting diodes with a p-type doped quantum barrier. *Optics Letters*, **2013**, 38, 202-4	3	29
121	Advantages of the Blue InGaN/GaN Light-Emitting Diodes with an AlGaN/GaN/AlGaN Quantum Well Structured Electron Blocking Layer. *ACS Photonics*, **2014**, 1, 377-381	6.3	28
120	On the origin of the electron blocking effect by an n-type AlGaN electron blocking layer. *Applied Physics Letters*, **2014**, 104, 073511	3.4	27
119	On the mechanisms of InGaN electron cooler in InGaN/GaN light-emitting diodes. *Optics Express*, **2014**, 22 Suppl 3, A779-89	3.3	26
118	Comparative study of field-dependent carrier dynamics and emission kinetics of InGaN/GaN light-emitting diodes grown on (112□2) semipolar versus (0001) polar planes. *Applied Physics Letters* , **2014**, 104, 143506	3.4	26
117	Polarization self-screening in [0001] oriented InGaN/GaN light-emitting diodes for improving the electron injection efficiency. *Applied Physics Letters*, **2014**, 104, 251108	3.4	25
116	Investigations on AlGaN-Based Deep-Ultraviolet Light-Emitting Diodes With Si-Doped Quantum Barriers of Different Doping Concentrations. *Physica Status Solidi - Rapid Research Letters*, **2018**, 12, 1700346	2.5	25
115	Progress in External Quantum Efficiency for III-Nitride Based Deep Ultraviolet Light-Emitting Diodes. *Physica Status Solidi (A) Applications and Materials Science*, **2019**, 216, 1800815	1.6	24
114	UVA light-emitting diode grown on Si substrate with enhanced electron and hole injections. *Optics Letters*, **2017**, 42, 4533-4536	3	23
113	On the Hole Injection for III-Nitride Based Deep Ultraviolet Light-Emitting Diodes. *Materials*, **2017**, 10,	3.5	23
112	p-doping-free InGaN/GaN light-emitting diode driven by three-dimensional hole gas. *Applied Physics Letters*, **2013**, 103, 263501	3.4	22
111	Very high external quantum efficiency and wall-plug efficiency 527 nm InGaN green LEDs by MOCVD. *Optics Express*, **2018**, 26, 33108-33115	3.3	21
110	Influence of n-type versus p-type AlGaN electron-blocking layer on InGaN/GaN multiple quantum wells light-emitting diodes. *Applied Physics Letters*, **2013**, 103, 053512	3.4	20
109	Nonradiative recombination--critical in choosing quantum well number for InGaN/GaN light-emitting diodes. *Optics Express*, **2015**, 23, A34-42	3.3	19
108	Establishment of the relationship between the electron energy and the electron injection for AlGaN based ultraviolet light-emitting diodes. *Optics Express*, **2018**, 26, 17977-17987	3.3	19
107	A hole modulator for InGaN/GaN light-emitting diodes. *Applied Physics Letters*, **2015**, 106, 063501	3.4	18
106	Enhanced the Optical Power of AlGaN-Based Deep Ultraviolet Light-Emitting Diode by Optimizing Mesa Sidewall Angle. *IEEE Photonics Journal*, **2018**, 10, 1-7	1.8	18
105	White light-emitting diodes based on carbon dots and Mn-doped CsPbMnCl nanocrystals. *Nanotechnology*, **2019**, 30, 245201	3.4	18

104	On the AlxGa1-xN/AlyGa1-yN/AlxGa1-xN (x>y) p-electron blocking layer to improve the hole injection for AlGaN based deep ultraviolet light-emitting diodes. *Superlattices and Microstructures*, **2018**, 113, 472-477	2.8	18
103	Promoted Hole Transport Capability by Improving Lateral Current Spreading for High-Efficiency Quantum Dot Light-Emitting Diodes. *Advanced Science*, **2020**, 7, 2001760	13.6	17
102	Polarization-enhanced AlGaN solar-blind ultraviolet detectors. *Photonics Research*, **2020**, 8, 1243	6	17
101	On the hole accelerator for III-nitride light-emitting diodes. *Applied Physics Letters*, **2016**, 108, 151105	3.4	17
100	Temperature-Dependent Efficiency Droop in GaN-Based Blue LEDs. *IEEE Electron Device Letters*, **2018**, 39, 528-531	4.4	16
99	Investigation of p-type depletion doping for InGaN/GaN-based light-emitting diodes. *Applied Physics Letters*, **2017**, 110, 033506	3.4	15
98	A PN-type quantum barrier for InGaN/GaN light emitting diodes. *Optics Express*, **2013**, 21, 15676-85	3.3	15
97	On the p-AlGaN/n-AlGaN/p-AlGaN Current Spreading Layer for AlGaN-based Deep Ultraviolet Light-Emitting Diodes. *Nanoscale Research Letters*, **2018**, 13, 355	5	15
96	On the internal quantum efficiency for InGaN/GaN light-emitting diodes grown on insulating substrates. *Physica Status Solidi (A) Applications and Materials Science*, **2016**, 213, 3078-3102	1.6	14
95	High-performance nanoporous-GaN metal-insulator-semiconductor ultraviolet photodetectors with a thermal oxidized □GaO layer. *Optics Letters*, **2019**, 44, 2197-2200	3	14
94	Simultaneous enhancement of electron overflow reduction and hole injection promotion by tailoring the last quantum barrier in InGaN/GaN light-emitting diodes. *Applied Physics Letters*, **2014**, 104, 161113	3.4	13
93	A dielectric-constant-controlled tunnel junction for III-nitride light-emitting diodes. *Physica Status Solidi (A) Applications and Materials Science*, **2017**, 214, 1600937	1.6	12
92	A review on the low external quantum efficiency and the remedies for GaN-based micro-LEDs. *Journal Physics D: Applied Physics*, **2021**, 54, 153002	3	12
91	Enhancing Both TM- and TE-Polarized Light Extraction Efficiency of AlGaN-Based Deep Ultraviolet Light-Emitting Diode via Air Cavity Extractor With Vertical Sidewall. *IEEE Photonics Journal*, **2018**, 10, 1-9	1.8	11
90	Effects of Meshed p-type Contact Structure on the Light Extraction Effect for Deep Ultraviolet Flip-Chip Light-Emitting Diodes. *Nanoscale Research Letters*, **2019**, 14, 149	5	10
89	Formation of "Steady Size" State for Accurate Size Control of CdSe and CdS Quantum Dots. *Journal of Physical Chemistry Letters*, **2017**, 8, 3576-3580	6.4	10
88	Low thermal-mass LEDs: size effect and limits. *Optics Express*, **2014**, 22, 32200-7	3.3	10
87	Three-dimensional band diagram in lateral polarity junction III-nitride heterostructures. *Optica*, **2019**, 6, 1058	8.6	10

86	Enhanced Optical Performance of AlGaN-Based Deep Ultraviolet Light-Emitting Diodes by Electrode Patterns Design. *IEEE Electron Device Letters*, **2019**, 40, 1925-1928	4.4	9
85	Doping-Induced Energy Barriers to Improve the Current Spreading Effect for AlGaN-Based Ultraviolet-B Light-Emitting Diodes. *IEEE Electron Device Letters*, **2020**, 1-1	4.4	9
84	Improving hole injection from p-EBL down to the end of active region by simply playing with polarization effect for AlGaN based DUV light-emitting diodes. *AIP Advances*, **2020**, 10, 065032	1.5	9
83	Polarization assisted self-powered GaN-based UV photodetector with high responsivity. *Photonics Research*, **2021**, 9, 734	6	9
82	A charge inverter for III-nitride light-emitting diodes. *Applied Physics Letters*, **2016**, 108, 133502	3.4	9
81	Different scattering effect of nano-patterned sapphire substrate for TM- and TE-polarized light emitted from AlGaN-based deep ultraviolet light-emitting diodes. *Optical Materials Express*, **2021**, 11, 729	2.6	9
80	High color rendering index and stable white light emitting diodes fabricated from lead bromide perovskites. *Applied Physics Letters*, **2019**, 115, 153103	3.4	8
79	Current Crowding Phenomenon: Theoretical and Direct Correlation With the Efficiency Droop of Light Emitting Diodes by a Modified ABC Model. *IEEE Journal of Quantum Electronics*, **2015**, 51, 1-9	2	8
78	Effects of Inclined Sidewall Structure With Bottom Metal Air Cavity on the Light Extraction Efficiency for AlGaN-Based Deep Ultraviolet Light-Emitting Diodes. *IEEE Photonics Journal*, **2017**, 9, 1-9	1.8	8
77	Integrating remote reflector and air cavity into inclined sidewalls to enhance the light extraction efficiency for AlGaN-based DUV LEDs. *Optics Express*, **2020**, 28, 17035-17046	3.3	8
76	Boosting the Efficiency and Stability of Perovskite Light-Emitting Devices by a 3-Amino-1-propanol-Tailored PEDOT:PSS Hole Transport Layer. *ACS Applied Materials & Interfaces*, **2020**, 12, 43331-43338	9.5	8
75	Highly efficient Mn-doped CsPb(Cl/Br) quantum dots for white light-emitting diodes. *Nanotechnology*, **2020**, 31, 065603	3.4	8
74	On the polarization effect of the p-EBL/p-AlGaN/p-GaN structure for AlGaN-based deep-ultraviolet light-emitting diodes. *Superlattices and Microstructures*, **2018**, 122, 280-285	2.8	7
73	Modulating the Layer Resistivity by Band-Engineering to Improve the Current Spreading for DUV LEDs. *IEEE Photonics Technology Letters*, **2019**, 31, 1201-1204	2.2	7
72	Enhanced Photoresponse of Indium-Doped Tin Disulfide Nanosheets. *ACS Applied Materials & Interfaces*, **2020**, 12, 2607-2614	9.5	7
71	Alternative Strategy to Reduce Surface Recombination for InGaN/GaN Micro-light-Emitting Diodes-Thinning the Quantum Barriers to Manage the Current Spreading. *Nanoscale Research Letters*, **2020**, 15, 160	5	7
70	The morphology evolution of selective area wet etched commercial patterned sapphire substrates. *Journal of Micromechanics and Microengineering*, **2019**, 29, 035012	2	7
69	Lead-free, stable orange-red-emitting hybrid copper based organic-inorganic compounds. *Dalton Transactions*, **2021**, 50, 2766-2773	4.3	7

68	Improved the AlGaN-Based Ultraviolet LEDs Performance With Super-Lattice Structure Last Barrier. *IEEE Photonics Journal*, **2018**, 10, 1-7	1.8	7
67	$8times8$ 4H-SiC Ultraviolet Avalanche Photodiode Arrays With High Uniformity. *IEEE Electron Device Letters*, **2019**, 40, 1591-1594	4.4	6
66	Design Strategies for Mesa-Type GaN-Based Schottky Barrier Diodes for Obtaining High Breakdown Voltage and Low Leakage Current. *IEEE Transactions on Electron Devices*, **2020**, 67, 1931-1938	2.9	6
65	Decoupling contact and mirror: an effective way to improve the reflector for flip-chip InGaN/GaN-based light-emitting diodes. *Journal Physics D: Applied Physics*, **2016**, 49, 265106	3	6
64	On the effect of N-GaN/P-GaN/N-GaN/P-GaN/N-GaN built-in junctions in the n-GaN layer for InGaN/GaN light-emitting diodes. *Optics Express*, **2014**, 22, 809-16	3.3	6
63	On the Impact of Electron Leakage on the Efficiency Droop for AlGaN Based Deep Ultraviolet Light Emitting Diodes. *IEEE Photonics Journal*, **2020**, 12, 1-7	1.8	6
62	On the origin for the hole confinement into apertures for GaN-based VCSELs with buried dielectric insulators. *Optics Express*, **2020**, 28, 8668-8679	3.3	6
61	Understanding omni-directional reflectors and nominating more dielectric materials for deep ultraviolet light-emitting diodes with inclined sidewalls. *Journal of Applied Physics*, **2020**, 128, 093106	2.5	6
60	The Effect of Sapphire Substrates on Omni-Directional Reflector Design for Flip-Chip Near-Ultraviolet Light-Emitting Diodes. *IEEE Photonics Journal*, **2019**, 11, 1-9	1.8	6
59	Numerical Investigations on the n+-GaN/AlGaN/p+-GaN Tunnel Junction for III-Nitride UV Light-Emitting Diodes. *Physica Status Solidi (A) Applications and Materials Science*, **2017**, 214, 1700624	1.6	5
58	Influence of an Insulator Layer on the Charge Transport in a Metal/Insulator/n-AlGaN Structure. *Physica Status Solidi (A) Applications and Materials Science*, **2019**, 216, 1800810	1.6	5
57	Optimization Strategy of 4H-SiC Separated Absorption Charge and Multiplication Avalanche Photodiode Structure for High Ultraviolet Detection Efficiency. *Nanoscale Research Letters*, **2019**, 14, 396	5	5
56	Interplay between various active regions and the interband transition for AlGaN-based deep-ultraviolet light-emitting diodes to enable a reduced TM-polarized emission. *Journal of Applied Physics*, **2019**, 126, 245702	2.5	5
55	On the Carrier Transport for InGaN/GaN Core-Shell Nanorod Green Light-Emitting Diodes. *IEEE Nanotechnology Magazine*, **2019**, 18, 176-182	2.6	5
54	Stable and highly efficient blue-emitting CsPbBr3 perovskite nanomaterials via kinetic-controlled growth. *Chemical Engineering Journal*, **2021**, 419, 129612	14.7	5
53	Artificially formed resistive ITO/p-GaN junction to suppress the current spreading and decrease the surface recombination for GaN-based micro-light emitting diodes. *Optics Express*, **2021**, 29, 31201-31211	3.3	5
52	Manipulation of Si Doping Concentration for Modification of the Electric Field and Carrier Injection for AlGaN-Based Deep-Ultraviolet Light-Emitting Diodes. *Crystals*, **2018**, 8, 258	2.3	4
51	Eco-Friendly and Efficient Luminescent Solar Concentrators Based on a Copper(I)-Halide Composite. *ACS Applied Materials & Interfaces*, **2021**, 13, 56348-56357	9.5	4

50	Three-dimensional metal–semiconductor–metal bipolar ultraviolet phototransistor based on GaN p-i-n epilayer. *Applied Physics Letters*, **2021**, 119, 161105	3.4	4
49	BAlN for III-nitride UV light-emitting diodes: undoped electron blocking layer. *Journal Physics D: Applied Physics*, **2021**, 54, 175104	3	4
48	Enhanced Photodetection Performance of Photodetectors Based on Indium-Doped Tin Disulfide Few Layers. *ACS Applied Materials & Interfaces*, **2021**, 13, 35889-35896	9.5	4
47	Enhancing the light extraction efficiency for AlGaN-based DUV LEDs with a laterally over-etched p-GaN layer at the top of truncated cones. *Optics Express*, **2021**, 29, 30532-30542	3.3	4
46	Metal-insulator-semiconductor structure for deep-ultraviolet light-emitting diodes to increase the electron injection in the cathode region. *Superlattices and Microstructures*, **2020**, 140, 106467	2.8	3
45	Improving the Current Spreading by Locally Modulating the Doping Type in the n-AlGaN Layer for AlGaN-Based Deep Ultraviolet Light-Emitting Diodes. *Nanoscale Research Letters*, **2019**, 14, 268	5	3
44	Improved InGaN/GaN light-emitting diodes with a p-GaN/n-GaN/p-GaN/n-GaN/p-GaN current-spreading layer: errata. *Optics Express*, **2013**, 21, 17670	3.3	3
43	Efficient and Stable Blue Perovskite Light-Emitting Devices Based on Inorganic CsPbBr Spaced Low-Dimensional CsPbBr through Synergistic Control of Amino Alcohols and Polymer Additives. *ACS Applied Materials & Interfaces*, **2021**, 13, 33199-33208	9.5	3
42	Multiple-quantum-well-induced unipolar carrier transport multiplication in AlGaN solar-blind ultraviolet photodiode. *Photonics Research*, **2021**, 9, 1907	6	3
41	Enhancing the lateral current injection by modulating the doping type in the p-type hole injection layer for InGaN/GaN vertical cavity surface emitting lasers. *Optics Express*, **2020**, 28, 18035-18048	3.3	2
40	Fabrication and Growth Mechanism of Uniform Suspended Perovskite Thin Films. *Crystal Growth and Design*, **2018**, 18, 5770-5779	3.5	2
39	Polarization Engineering to Manipulate the Breakdown Voltage for GaN-Based PIN Diodes. *Physica Status Solidi (A) Applications and Materials Science*, **2019**, 216, 1900210	1.6	2
38	Synthesis of Quantum Dot-ZnS Nanosheet Inorganic Assembly with Low Thermal Fluorescent Quenching for LED Application. *Materials*, **2017**, 10,	3.5	2
37	128-pixel arrays of 4H-SiC UV APD with dual-frequency PECVD SiN passivation. *Optics Express*, **2020**, 28, 29245-29252	3.3	2
36	Numerical investigations into polarization-induced self-powered GaN-based MSM photodetectors.. *Applied Optics*, **2021**, 60, 10975-10983	1.7	2
35	Perovskite energy funnels for efficient white emission. *Journal of Colloid and Interface Science*, **2021**, 608, 1202-1211	9.3	2
34	Demonstration of ohmic contact using ${{rm MoO}_{rm x}}/{rm Al}$MoO/Al on p-GaN and the proposal of a reflective electrode for AlGaN-based DUV-LEDs. *Optics Letters*, **2020**, 45, 2427-2430	3	2
33	Improving the Current-Spreading Effect for GaN-Based Quasi-Vertical PIN Diode by Using an Embedded PN Junction. *Physica Status Solidi (A) Applications and Materials Science*, **2020**, 217, 2000146	1.6	2

32	Direct demonstration of carrier distribution and recombination within step-bunched UV-LEDs. *Photonics Research*, **2021**, 9, 764	6	2
31	Reducing the polarization mismatch between the last quantum barrier and p-EBL to enhance the carrier injection for AlGaN-based DUV LEDs. *Optical Materials Express*, **2021**, 11, 1713	2.6	2
30	Interface and photoluminescence characteristics of graphene-(GaN/InGaN)n multiple quantum wells hybrid structure. *Journal of Applied Physics*, **2016**, 119, 143105	2.5	2
29	On the Importance of the Polarity for GaN/InGaN Last Quantum Barriers in III-Nitride-Based Light-Emitting Diodes. *IEEE Photonics Journal*, **2016**, 8, 1-7	1.8	2
28	Aluminum doping effects on photoresponse characteristics of hydrothermal tin disulfide nanosheets. *CrystEngComm*, **2021**, 23, 4694-4699	3.3	2
27	Polarization Self-Screened Multiple Quantum Wells for Deep Ultraviolet Light-Emitting Diodes to Enhance the Optical Power. *IEEE Photonics Journal*, **2021**, 1-1	1.8	2
26	Deep Ultraviolet LEDs. *SpringerBriefs in Applied Sciences and Technology*, **2019**,	0.4	1
25	Effectively Confining the Lateral Current Within the Aperture for GaN Based VCSELs by Using a Reverse Biased NP Junction. *IEEE Journal of Quantum Electronics*, **2020**, 56, 1-7	2	1
24	Highly efficient and stable Eu3+-doped two-dimensional perovskites. *Journal of Alloys and Compounds*, **2022**, 902, 163841	5.7	1
23	Advantage of SiO2 Intermediate Layer on the Electron Injection for Ti/n-Al0.60Ga0.40N Structure. *IEEE Transactions on Electron Devices*, **2020**, 67, 3548-3552	2.9	1
22	Advances of beveled mesas for GaN-based trench Schottky barrier diodes. *AIP Advances*, **2021**, 11, 045316	1.65	1
21	High-Performance Triangular Miniaturized-LEDs for High Current and Power Density Applications. *ACS Photonics*, **2021**, 8, 2304-2310	6.3	1
20	Atmospheric Aerosol Multiband Synthesis Imaging Spectrometer. *Applied Spectroscopy*, **2019**, 73, 221-228	1.91	1
19	Enhanced photodetection performance of Schottky Pt/SnS2/Al and Au/SnS2/Al photodetectors. *Journal of Materials Chemistry C*, **2021**, 9, 10472-10477	7.1	1
18	Is a thin p-GaN layer possible for making high-efficiency AlGaN-based deep-ultraviolet light-emitting diodes?. *Optics Express*, **2021**, 29, 29651-29660	3.3	1
17	Sheet Charge Engineering Towards an Efficient Hole Injection in 290 nm Deep Ultraviolet Light-Emitting Diodes. *IEEE Photonics Journal*, **2021**, 13, 1-8	1.8	1
16	Simulation study for GaN-based hybrid trench MOS barrier Schottky diode with an embedded p-type NiO termination: increased forward current density and enhanced breakdown voltage. *Japanese Journal of Applied Physics*, **2022**, 61, 014002	1.4	0
15	Enhanced performance of an AlGaN-based deep ultraviolet light-emitting diode using a p-GaN/SiO/ITO tunnel junction.. *Optics Letters*, **2022**, 47, 798-801	3	0

14	On the impact of a metal-insulator-semiconductor structured n-electrode for AlGaN-based DUV LEDs.. *Applied Optics*, **2021**, 60, 11222-11226	1.7	0
13	Screen the Polarization Induced Electric Field Within the MQWs for DUV LEDs. *SpringerBriefs in Applied Sciences and Technology*, **2019**, 43-57	0.4	0
12	Strain-Reduced Micro-LEDs Grown Directly Using Partitioned Growth. *Frontiers in Chemistry*, **2021**, 9, 639023	5	0
11	Step-type quantum wells with slightly varied InN composition for GaN-based yellow micro light-emitting diodes. *Applied Optics*, **2021**, 60, 3006-3012	1.7	0
10	Hybrid metal/GaO/GaN ultraviolet detector for obtaining low dark current and high responsivity.. *Optics Letters*, **2022**, 47, 1561-1564	3	0
9	A Buried High k Insulator for Suppressing the Surface Recombination for GaN-Based Micro-Light-Emitting Diodes. *IEEE Transactions on Electron Devices*, **2022**, 1-4	2.9	0
8	Improve the Hole Injection to Enhance the IQE for DUV LEDs. *SpringerBriefs in Applied Sciences and Technology*, **2019**, 11-31	0.4	
7	Improved carrier confinement and stimulated recombination rate in GaN-based vertical-cavity surface-emitting lasers with buried p-AlGaN inversion layer. *Superlattices and Microstructures*, **2020**, 146, 106654	2.8	
6	Enhance the Electron Injection Efficiency for DUV LEDs. *SpringerBriefs in Applied Sciences and Technology*, **2019**, 33-42	0.4	
5	The Light Extraction Efficiency for DUV LEDs. *SpringerBriefs in Applied Sciences and Technology*, **2019**, 61-65	0.4	
4	On the Light Extraction Efficiency for III-Nitride-Based Light-Emitting Diodes. *Solid State Lighting Technology and Application Series*, **2019**, 311-335	0.7	
3	Tuning the Plasmonic Resonance Peak for Al Nanorods on AlGaN Layer to Deep Ultraviolet Band. *IEEE Photonics Journal*, **2021**, 1-1	1.8	
2	3-D Simulation Study of a Normally-OFF GaN Lateral Multi-Channel JFET With Optimized Electrical Field Transfer Terminal Structure. *IEEE Transactions on Electron Devices*, **2022**, 69, 1918-1923	2.9	
1	Improving the performance for flip-chip AlGaN-based deep ultraviolet light-emitting diodes using surface textured Ga-face n-AlGaN. *Optics Express*, **2022**, 30, 17781	3.3	